

## Supplementary Materials

# Electrochemical Etching-Assisted Fabrication of Quantum Tunneling Sensing Probes with Controlled Nanogap Width

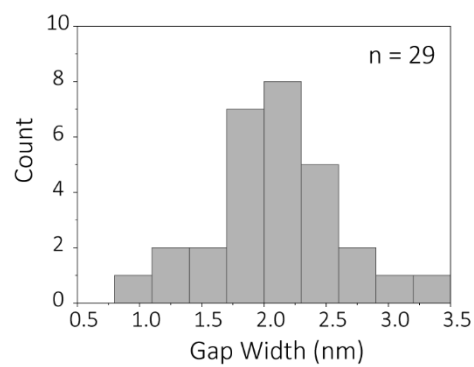
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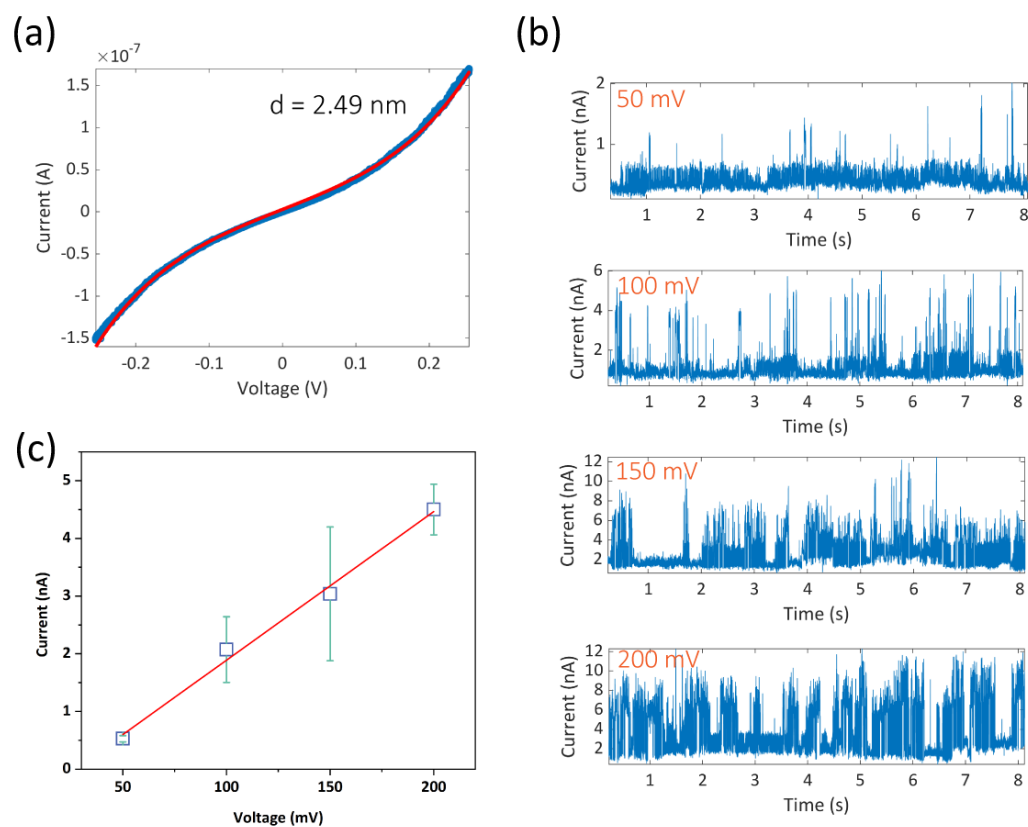
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**Figure S1.** Histogram of gap width distribution for etched-tunneling electrodes.



**Figure S2.** Tunneling current measurement of GOD under different bias voltage. (a) Tunneling current measurement of the used tunneling electrode and corresponding fit obtained by Simons model. (b) Representative tunneling current-time trace under different bias voltage for 10 nmol/L GOD in 0.01 mol/L PBS solution (pH 7.4). (c) Plots of peak current versus bias voltage for data presented in (b). All error bars represent 1 standard deviation from the mean.